

A
Final

providing a rotatable stamp having relief geometries on its surface to define a stamping surface;

applying ink to the surface of the rotatable stamp to define an inked stamping surface;

rotating the rotatable stamp as the substrate is placed in contact with the stamp to impress an inked pattern on the substrate as defined by the inked stamping surface; and

patterning the substrate by etching material from or depositing material on the substrate, wherein the inked stamping surface guides the etching or depositing of material in a geometry to define the patterned layer useful in fabricating an electronic device; and

removing the inked pattern from the substrate.

A2 *Sub B3*
Cancel claim 2.

Amend claim 8:

A2 *Sub B3*
8.(Amended) The method of claim 1 in which the step of patterning the substrate comprises etching material from the substrate applying an etchant selected from the group consisting of aqueous [ferri/]ferrocyanide, $K_4Fe(CN)_6$, $K_3Fe(CN)_6$, $Na_2S_2O_3$, and KOH in H_2O .

Amend claim 11:

A3 *Sub B5*
11.(Amended) The method of claim 10, in which the substrate further has an adhesive layer applied to the metallic layer selected from the group consisting of Ti and Cr.

Claim 12, line 1, delete "2" and substitute --1--.

Amend claim 13:

A4

13. A method for forming at least one layer on a substrate for use in fabricating an electronic device, the method comprising the steps of:

providing the substrate in the form of a flexible sheet;

providing a rotatable stamp mounted on an axle, the stamp having an outer surface with relief geometries with features having a resolution of about 30 μm or smaller to define a stamping surface;

rotating the rotatable stamp on an inking pad to apply ink to the stamp and define an inked stamping surface;

rotating the rotatable stamp as the substrate is placed in contact with the stamp so that an inked pattern corresponding to the inked stamping surface is formed on the substrate[, and];

passing the substrate to an apparatus for etching metal [material] from or depositing metal [material] on the substrate, wherein the inked stamping surface guides the etching of the metal [material] or depositing of the metal [material] in a geometry that defines an electrode [a] pattern on the substrate;

removing the inked stamping surface from the substrate; and

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applying semiconducting and dielectric layers over the electrode pattern to form the electrode device.

Cancel claims 16, 17 and 18.

Add claim 19:

19.(New) The method of claim 3 wherein the member comprises a cylinder with a glass surface.

Add claim 20:

A4

20.(New) The method of claim 1 wherein the step of patterning the substrate comprises patterning a layer of metal and further comprising the step of adding to the substrate a layer of organic semiconductor after removing the inked pattern.

Add claim 21:

A1

21.(New) A method of making an electronic device including a transistor comprising the steps of:

providing a semiconductor substrate having an insulating surface layer;
forming source and drain electrodes on the insulating surface layer by the process of claim 1, the electrodes separated by less than about one micrometer; and

depositing a semiconductor layer over the source and drain electrodes.

Add claim 22:

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22.(New) A method of making an electronic device including a transistor comprising the steps of:

providing a substrate;
forming source and drain electrodes on the substrate by the process of claim 1, the electrodes separated by less than about one micrometer;
disposing over the electrodes a semiconductor layer of organic material;
disposing over the semiconducting layer an insulating layer of organic material having a thickness less than about 1 micrometer; and
forming a gate electrode on the insulating layer overlying the region between the source and drain electrodes.